

Enabling TB-Class and GB/s-Performance SSDs with HLNAND™

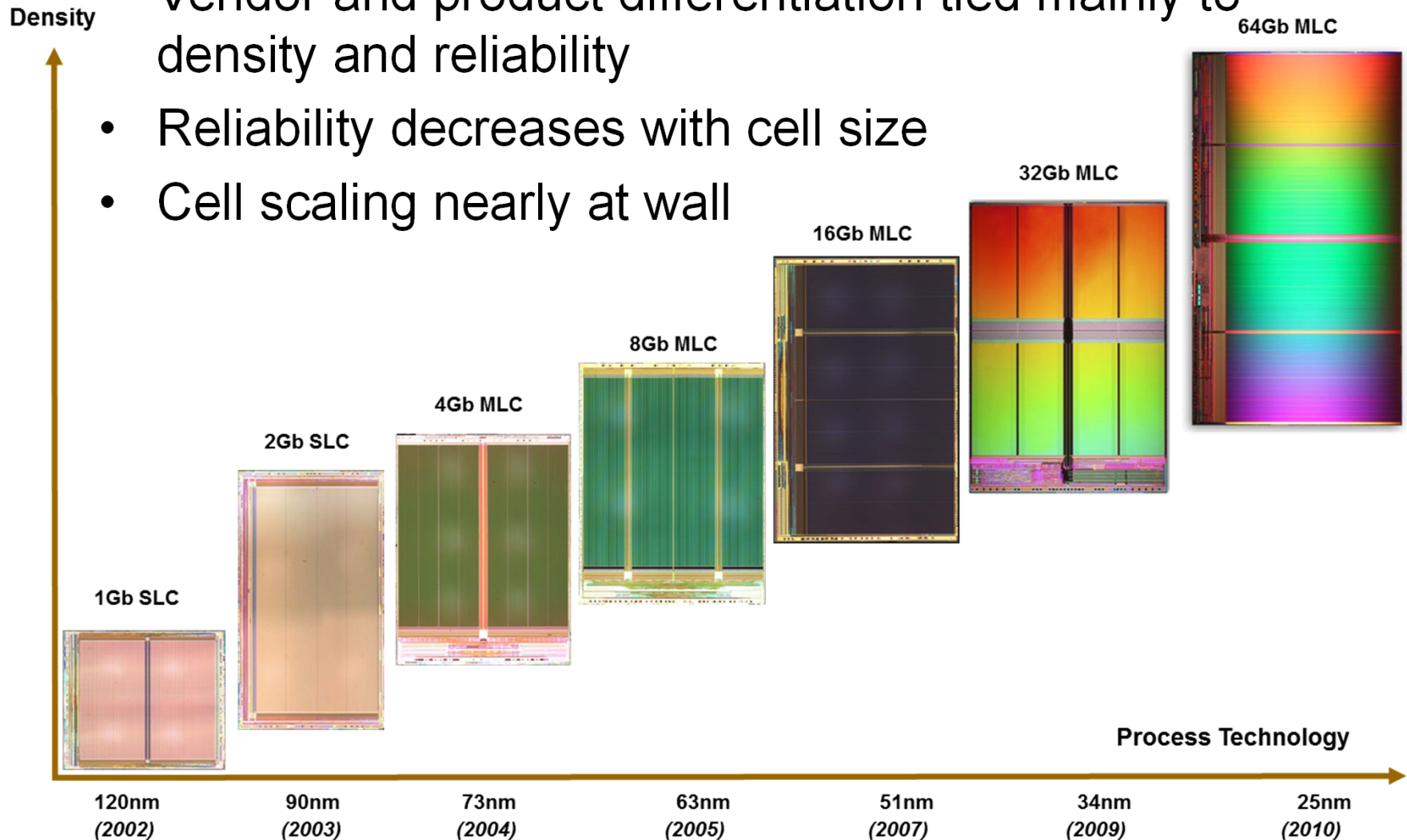
November 2011

Agenda

- Introduction
- HyperLink NAND (HLNAND)
Flash Technology
- Signal Integrity
- Summary

NAND Flash History

- Vendor and product differentiation tied mainly to density and reliability
- Reliability decreases with cell size
- Cell scaling nearly at wall



Nearly at Scaling Wall, What's Next?

- How will Flash producers make a compelling story at the wall?
- Reliability will still play a differentiating role
- Feature enrichment and performance improvements will also help distinguish products and serve product niches

Flash Market Landscape

Established

Consumer

- USB Drives
- Digital Cameras
- MP3
- Digital Camcorders
- GPS
- Gaming
- E-Books

- E-Books
- Gaming

Growing

Mobile

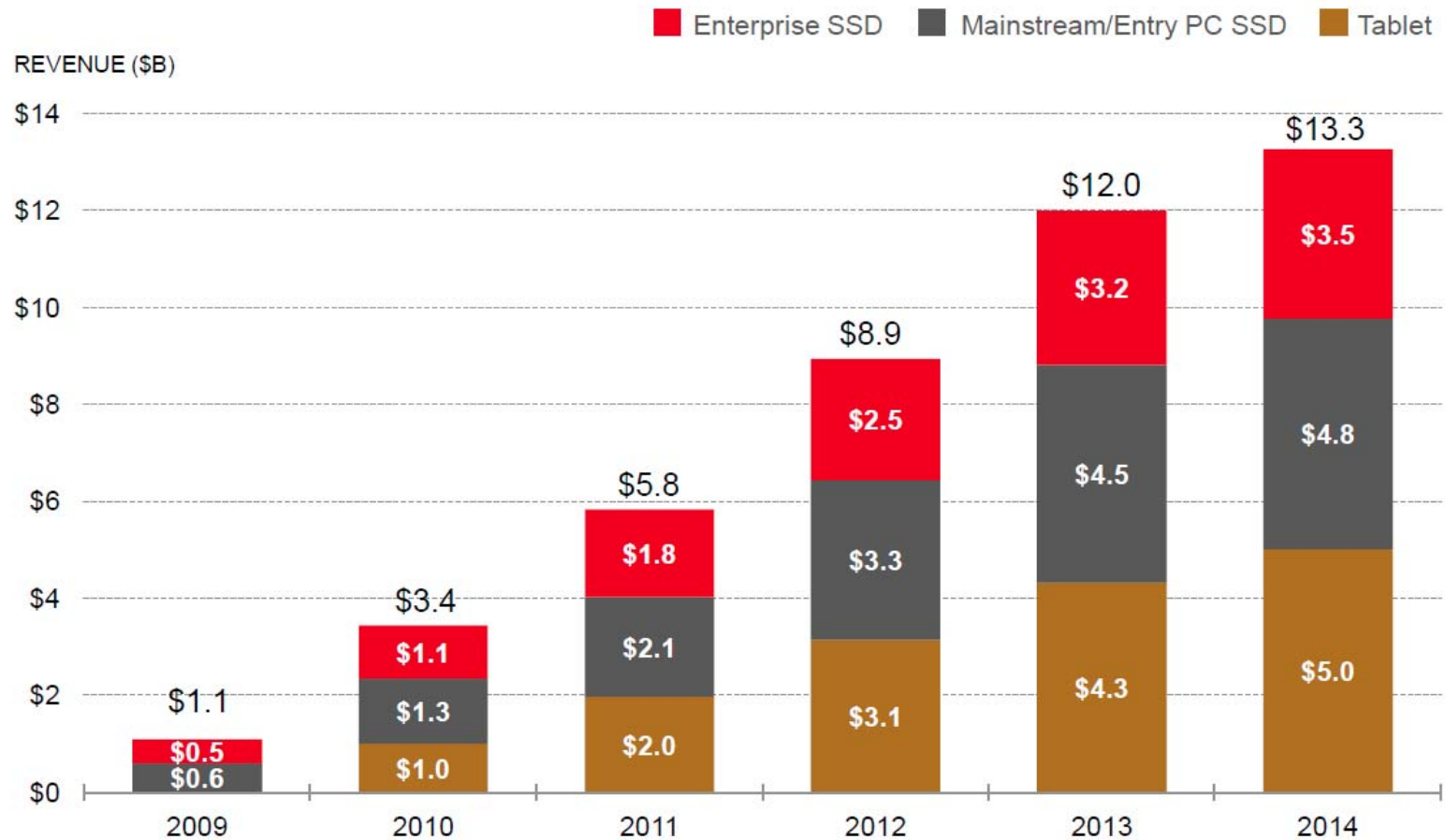
- Smartphones
- Featurephones

Emerging

Computing

- Netbooks
- Notebooks
- Gaming PCs
- Tablets
- Enterprise
- Cloud

Flash-based Emerging Market



Source: Gartner November, 2010; Semiconductor Forecast Worldwide—Forecast Database [SEQS-WW-DB-DATA]
Numbers are preliminary and subject to change

Source: SanDisk Feb 2011

Consumer SSD Market

200+ SSD vendors, but little differentiation



Enterprise-Grade Storage SSDs

Critical Factors:

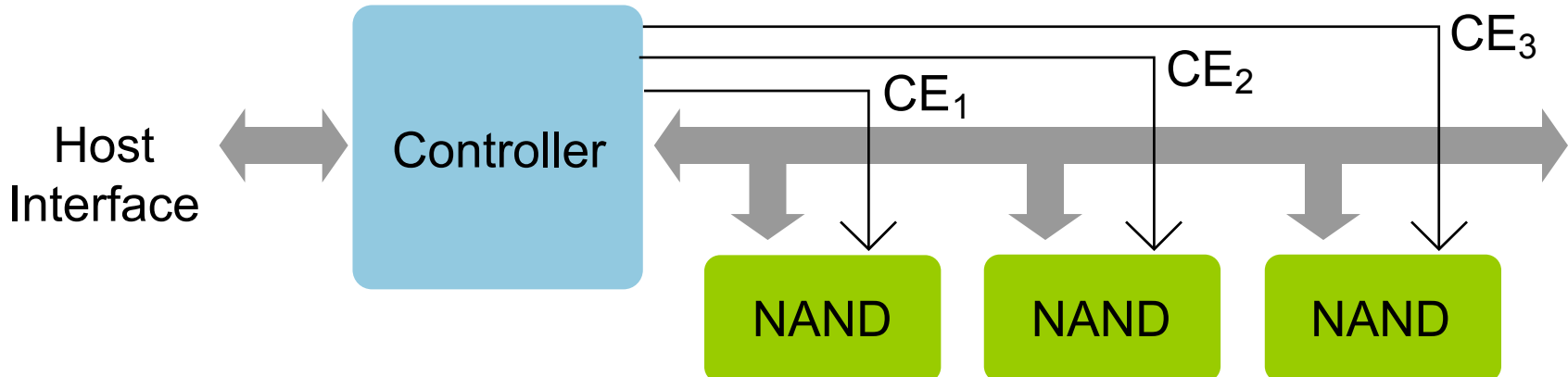
- Reliability
- Performance/Power
(High IOPS & Throughput)
- Scalability

Agenda

- Introduction
- **HyperLink NAND (HLNAND)
Flash Technology**
- Signal Integrity
- Summary

Conventional NAND Flash Interface

- 8 bit, bidirectional, multi-drop bus
- Asynchronous LVTTTL signaling up to 40Mb/s/pin
- Speed degradation with more than 4 devices on bus
- Chip Enable (CE) signal required for each device
- Power hungry 3.3V I/O or 1.8V I/O
- Recently DDR NAND (ONFI, Toggle) introduced

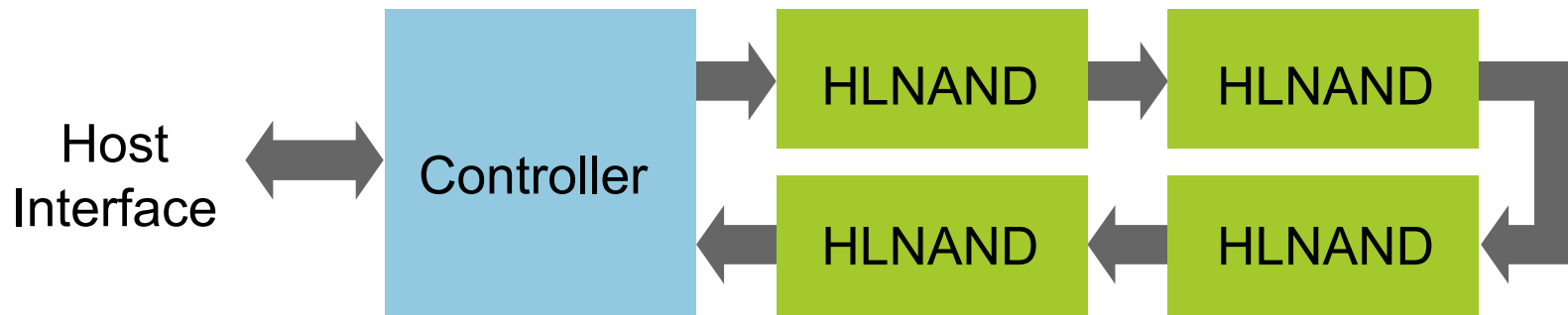


Performance and Scalability (Multi-drop Bus)

- Adding more channels:
 - System design complexity
 - Poor Signal Integrity (SI)
 - Higher power consumption
 - ECC/IO overhead per channel
 - Complex PCB design requiring 7-10 layers
- Adding more devices per channel:
 - Compromise between performance and # of devices

HLNAND Topology

- Daisy-chain, point-to-point connection – ring topology
- Cleaner signaling than multi-drop bus
- High speed and no-roll-off with increasing load



Performance and Scalability

(HLNAND Ring Topology)

- Higher performance 800MB/s and beyond (compared to 200MB/s & 400MB/s for conventional architecture)
- Virtually unlimited number of devices can be cascaded (higher number of ways per channel)
- Minimizing the number of channels per system

Performance and Scalability

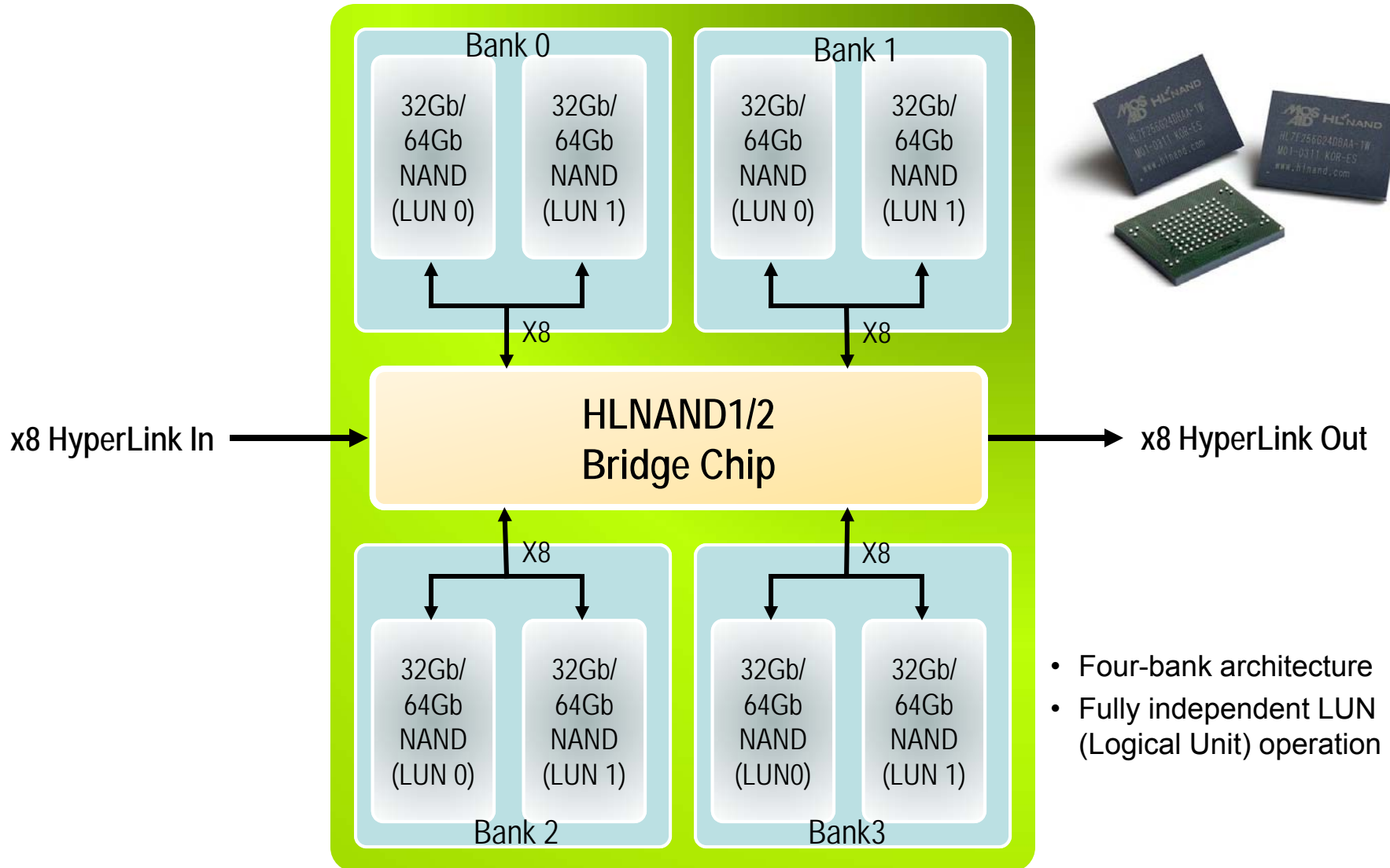
(HLNAND Ring Topology)

- Superior signal integrity (SI)
- No ODT required
- Statistically 50% lower power consumption per channel due to power-saving feature
- Scalable without diminishing performance for Tera Byte-Class & GB/s-Performance SSDs

HLNAND Parts

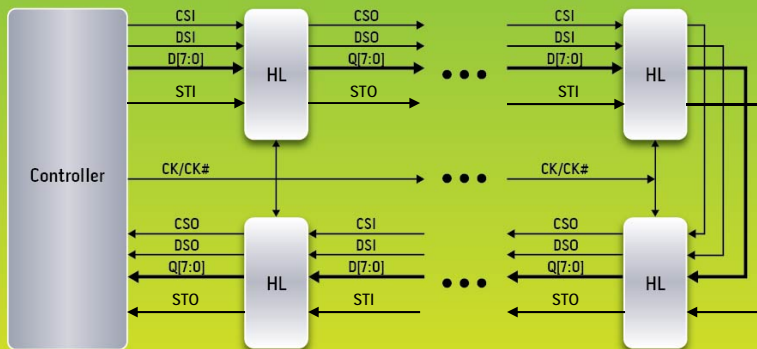
	HLNAND 1.0 (DDR266)	HLNAND 2.0 (DDR533/667/800)
E/S Sample	Available	Available
HLNAND Interface Chip	TSMC 180nm	TSMC 90nm
NAND Core	32nm/2xnm Async. or DDR-type NAND	32nm/2xnm Async. or DDR-type NAND
MCP Memory Capacity	128Gb ~ 1Tb (4 ~ 16 die stacked)	128Gb ~ 1Tb (4 ~ 16 die stacked)
I/O Data Rate	266 MB/s	533/667/800 MB/s
Package	14mm x 18mm 100-ball BGA	14mm x 18mm 100-ball BGA

HL & HL2 MCP Architecture



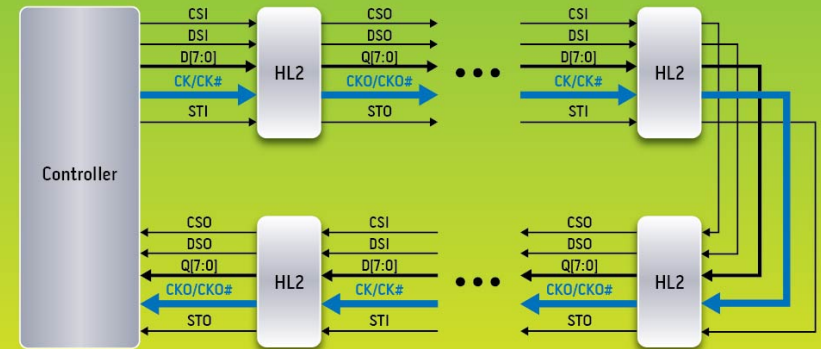
HLNAND vs. HLNAND2

HLNAND (HL1)



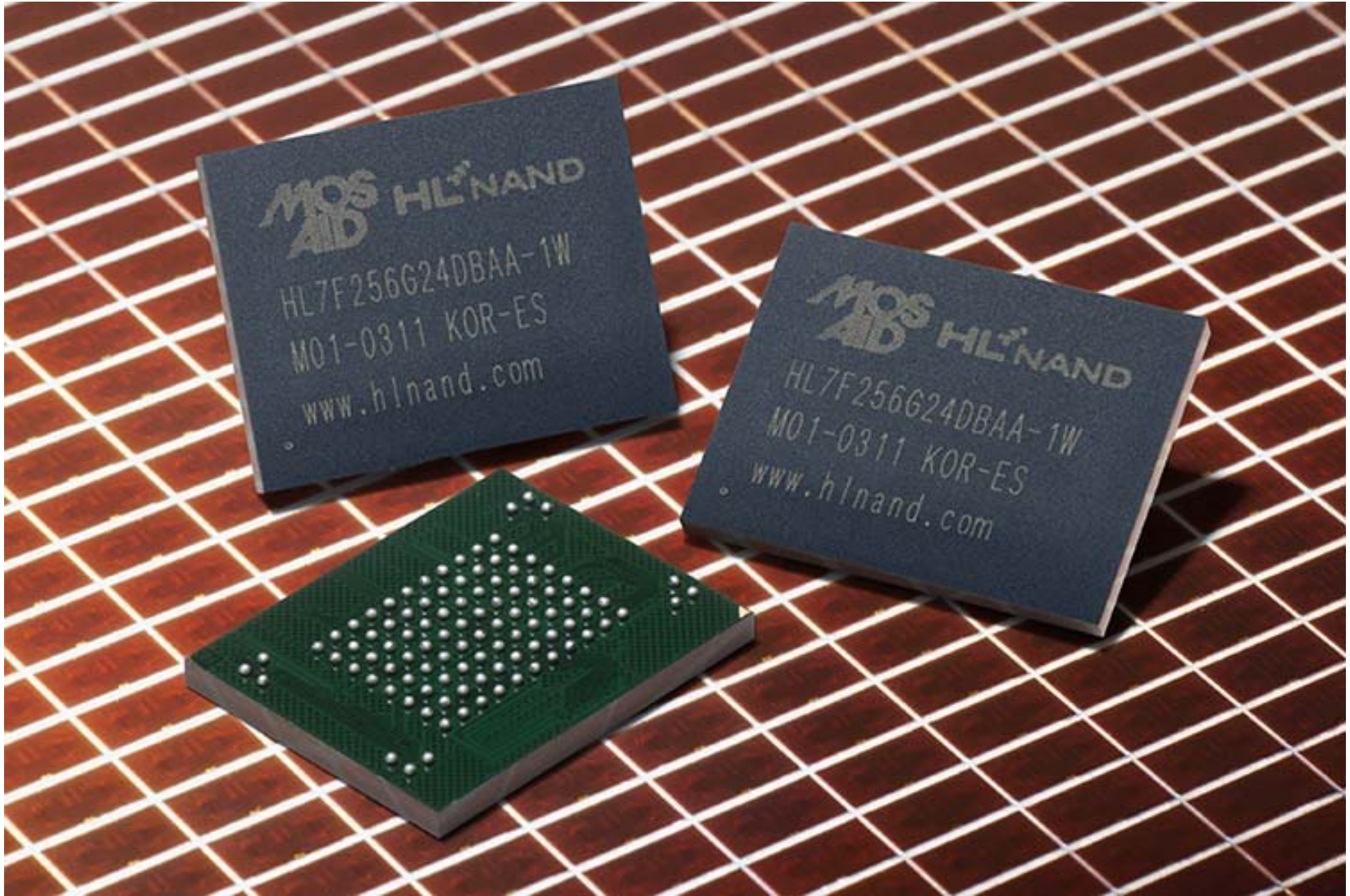
- Up to DDR-266
- Parallel distributed clock
- 1.8V LVCMOS

HLNAND2 (HL2)



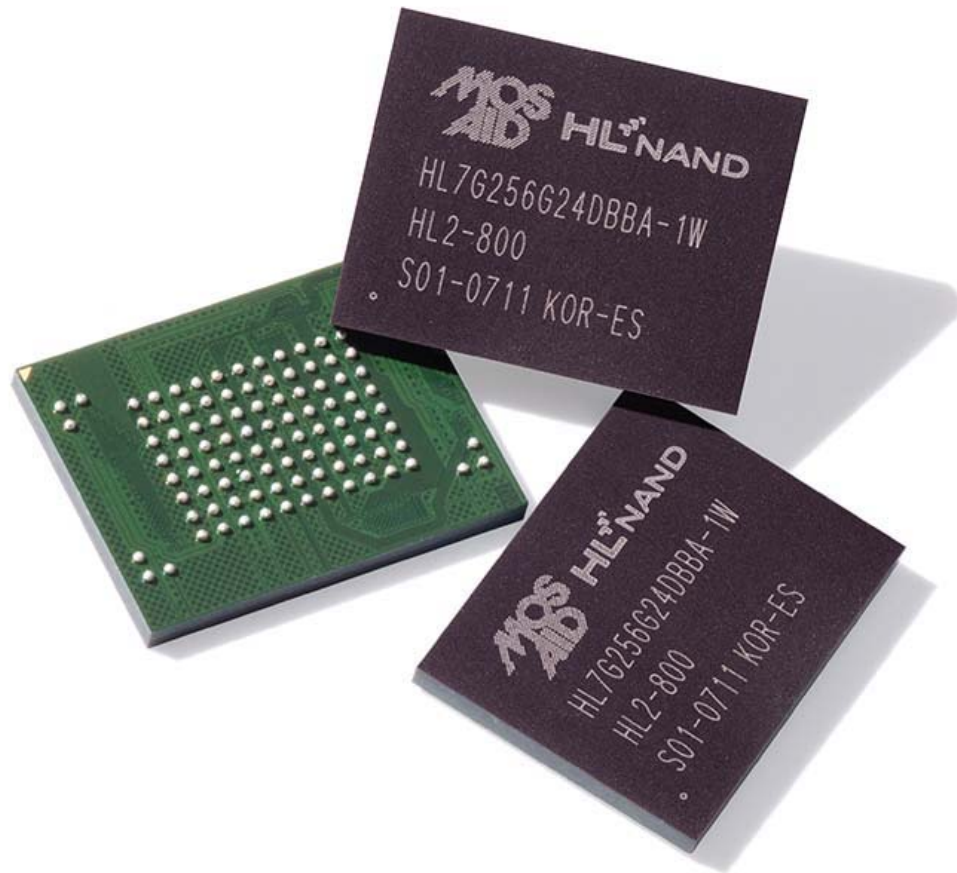
- DDR-533/DDR-667/DDR-800
- Source-synchronous differential clock
- JEDEC 1.2V HSUL_12

256Gb HLNAND E/S in 2011

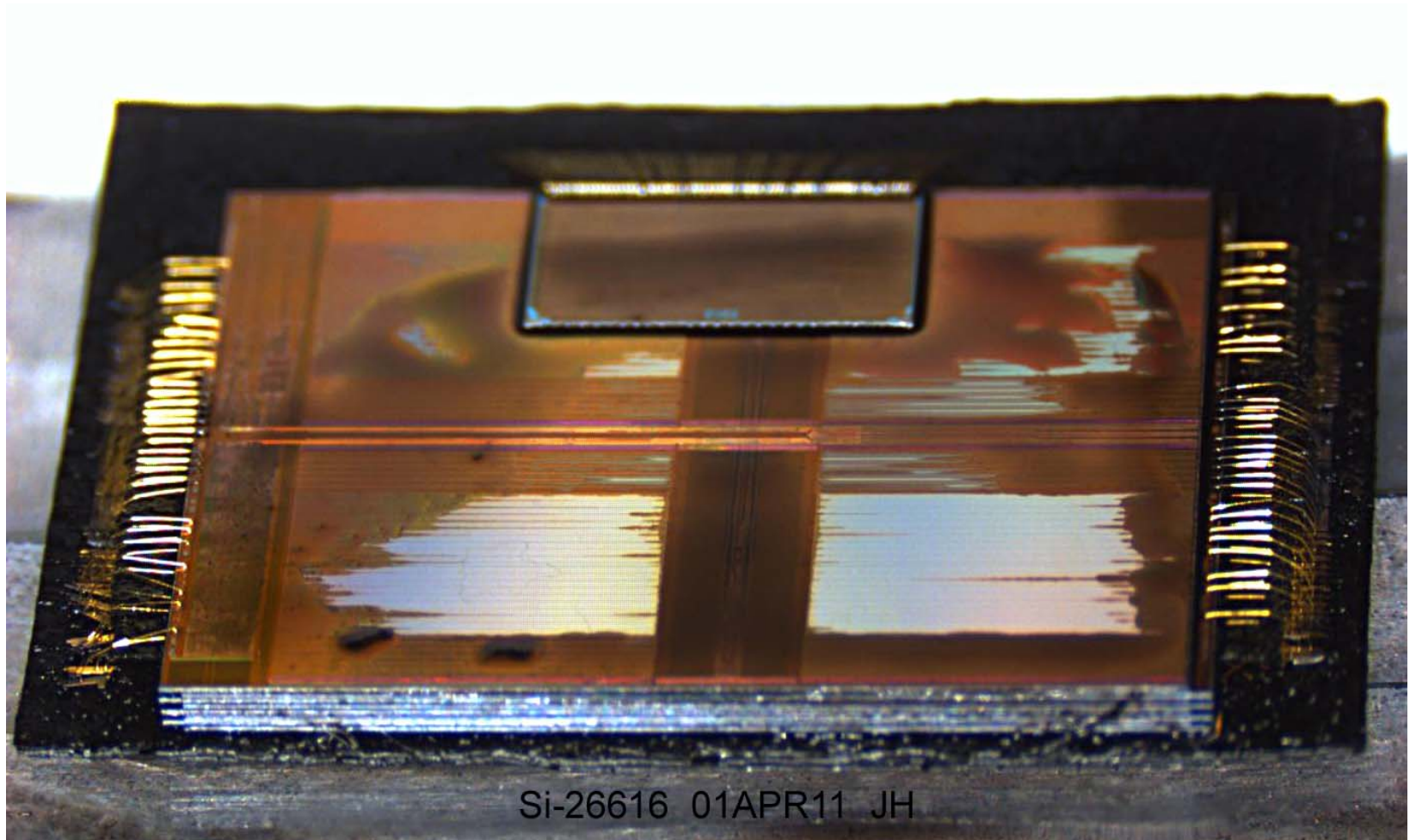


256Gb HLNAND2 E/S in 2011

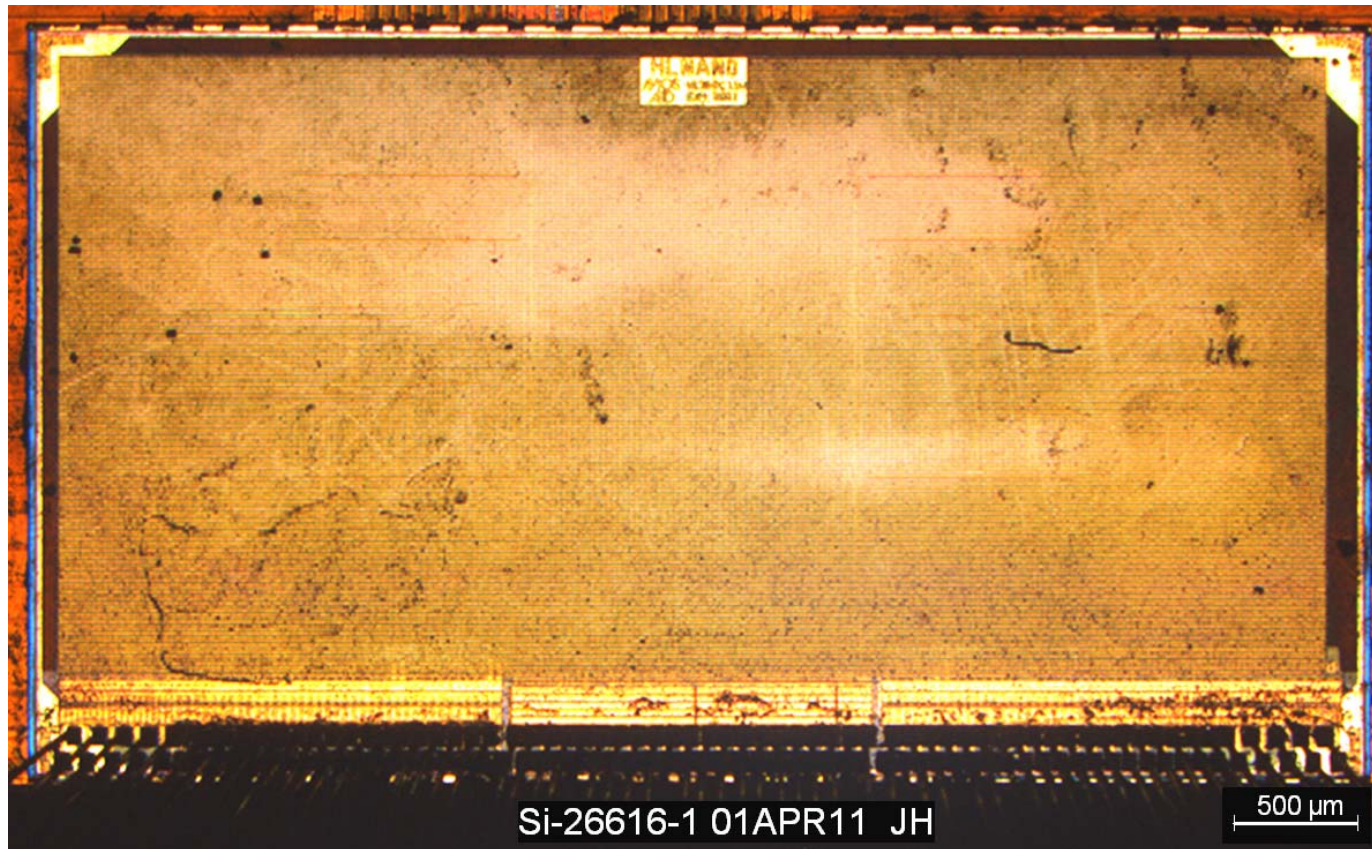
- Achieved fully working engineering sample of 256Gb HLNAND2 in Sep 2011



HLNAND: 9-die Stacked View

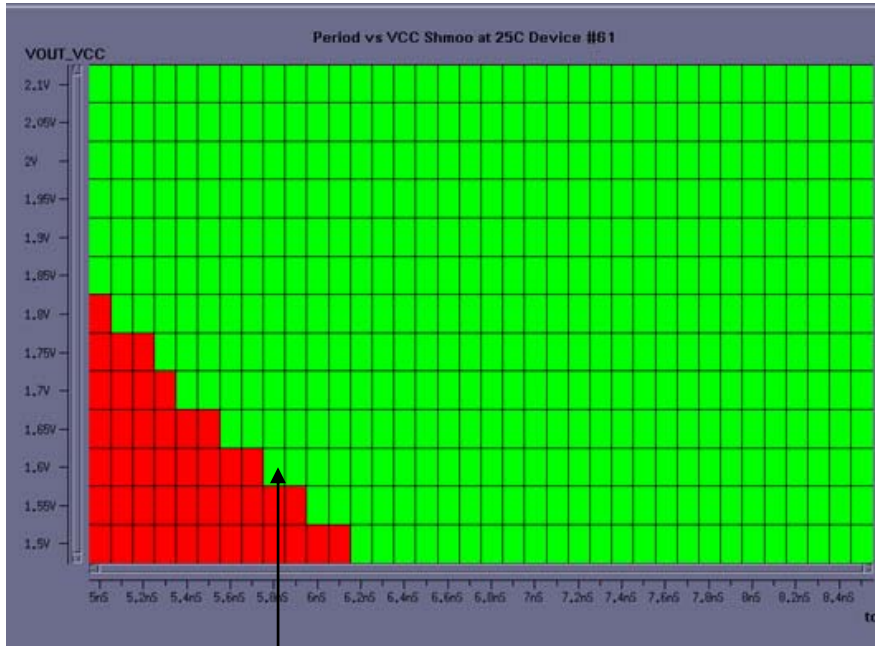


HLNAND Interface Chip



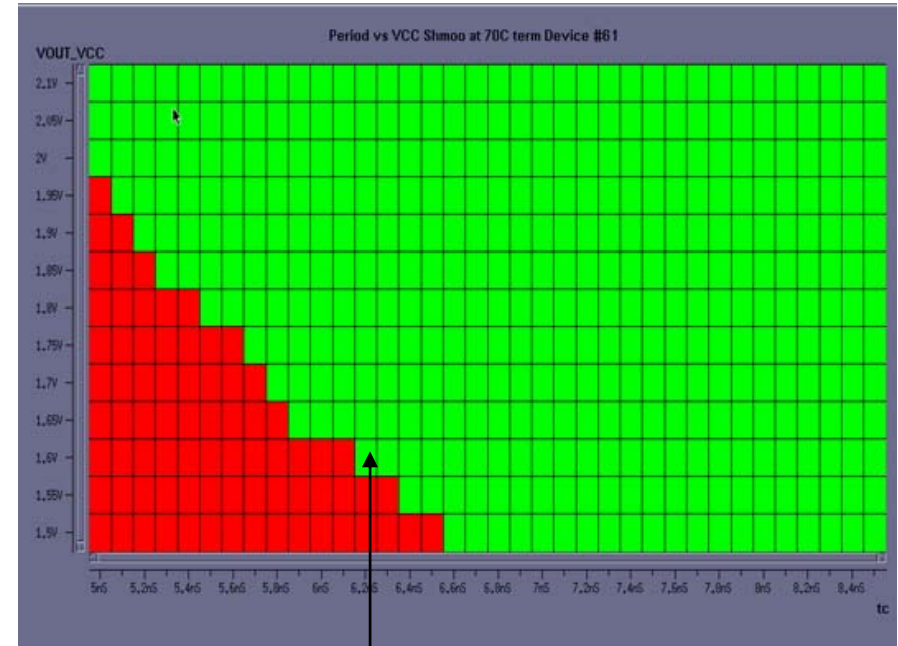
256Gb HLNAND Performance (DDR266 Grade)

@1.6V and Room Temp.



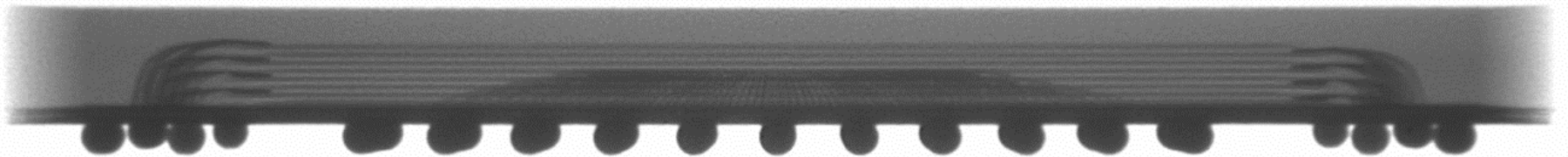
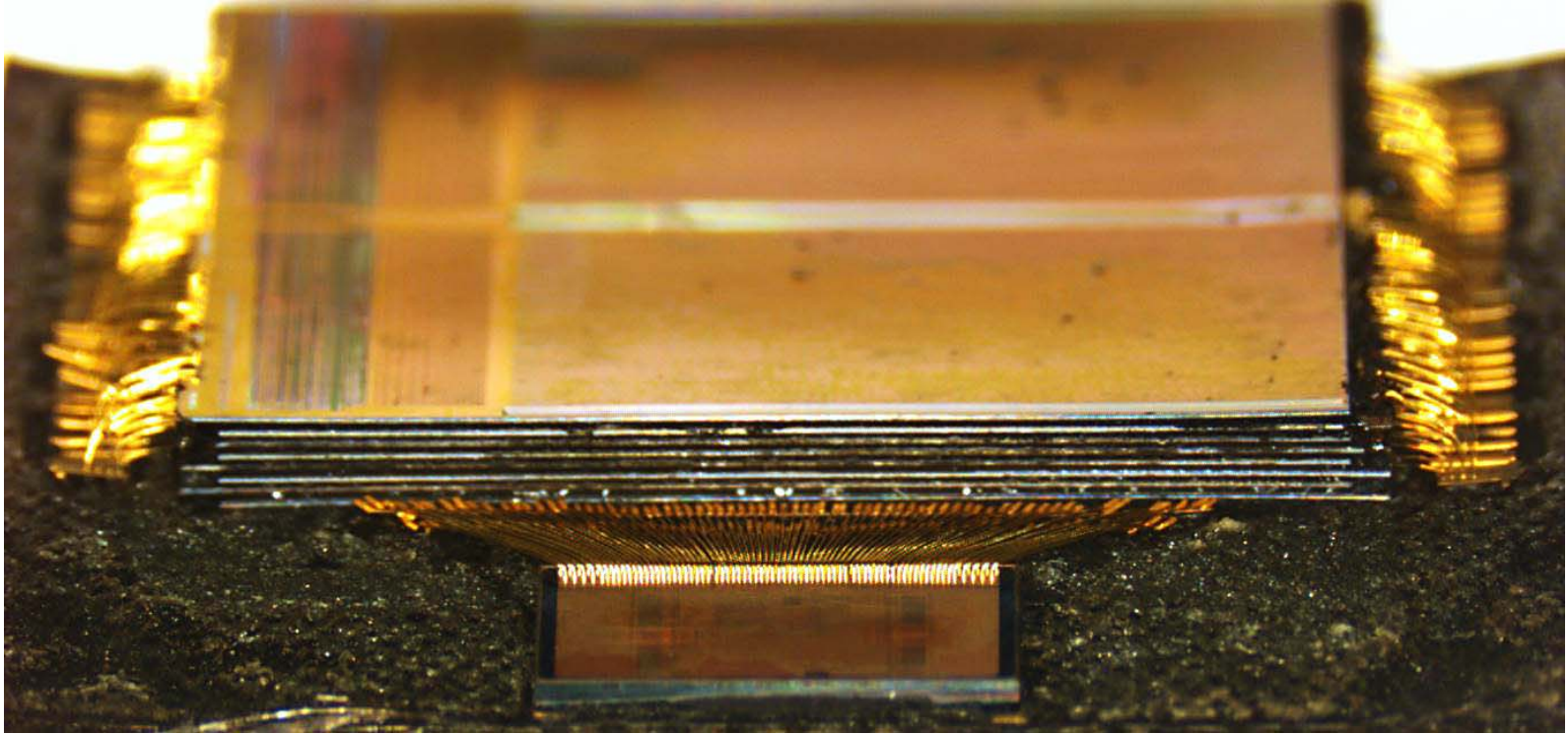
DDR-346 @173MHz

@1.6V and 70°C



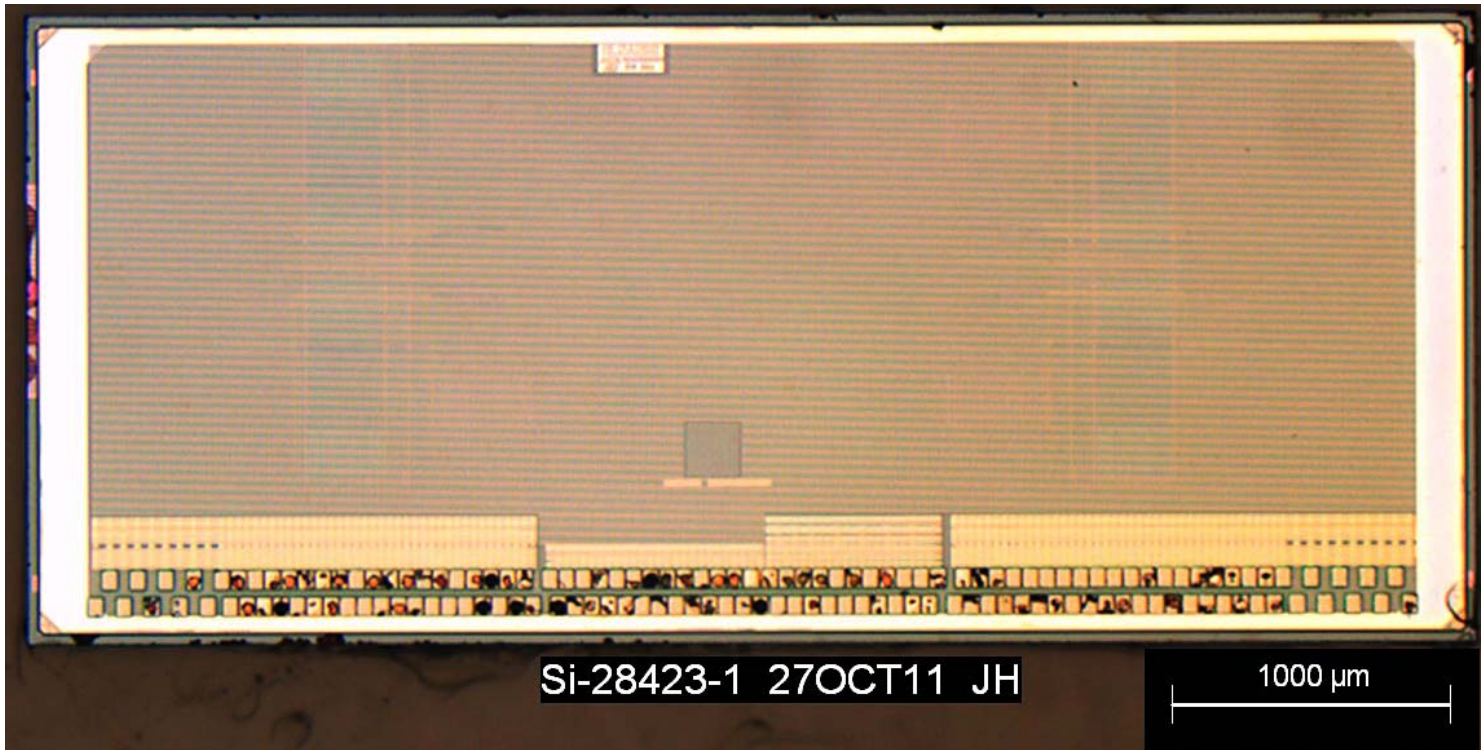
DDR-322 @161MHz

HLNAND2: (8+1)-die Stacked View



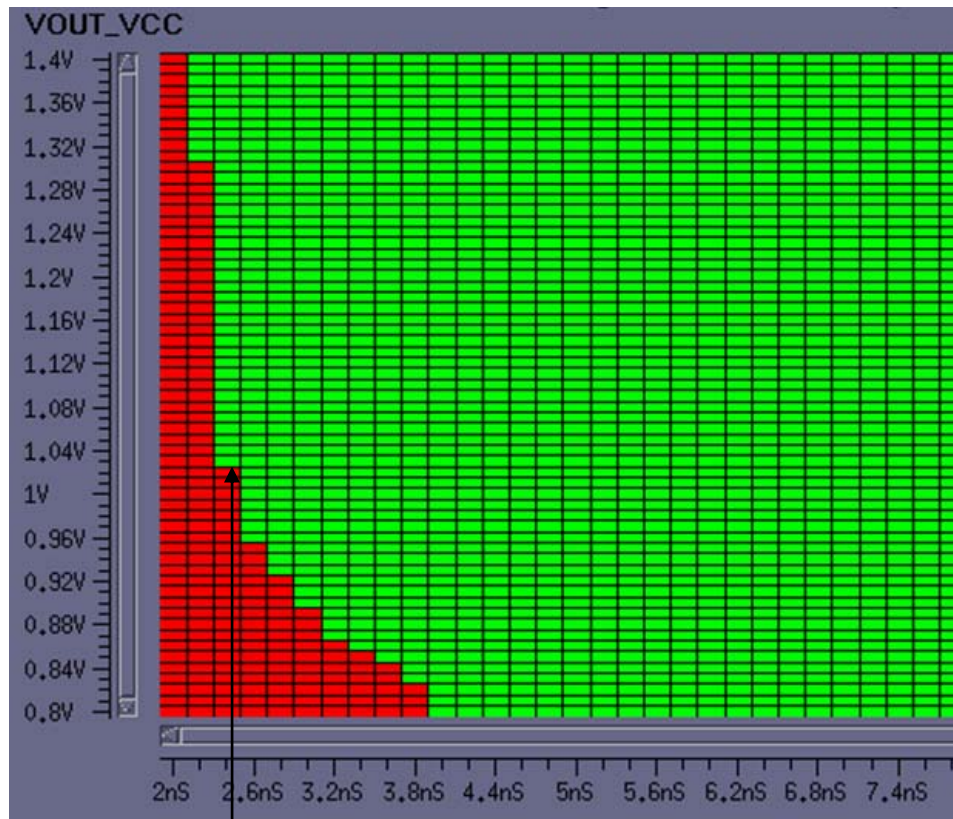
HLNAND2 Interface Chip

- Die Size = 5mm x 2mm = 10mm²



256Gb HLNAND2 Performance (DDR800 Grade)

@ Room Temp.



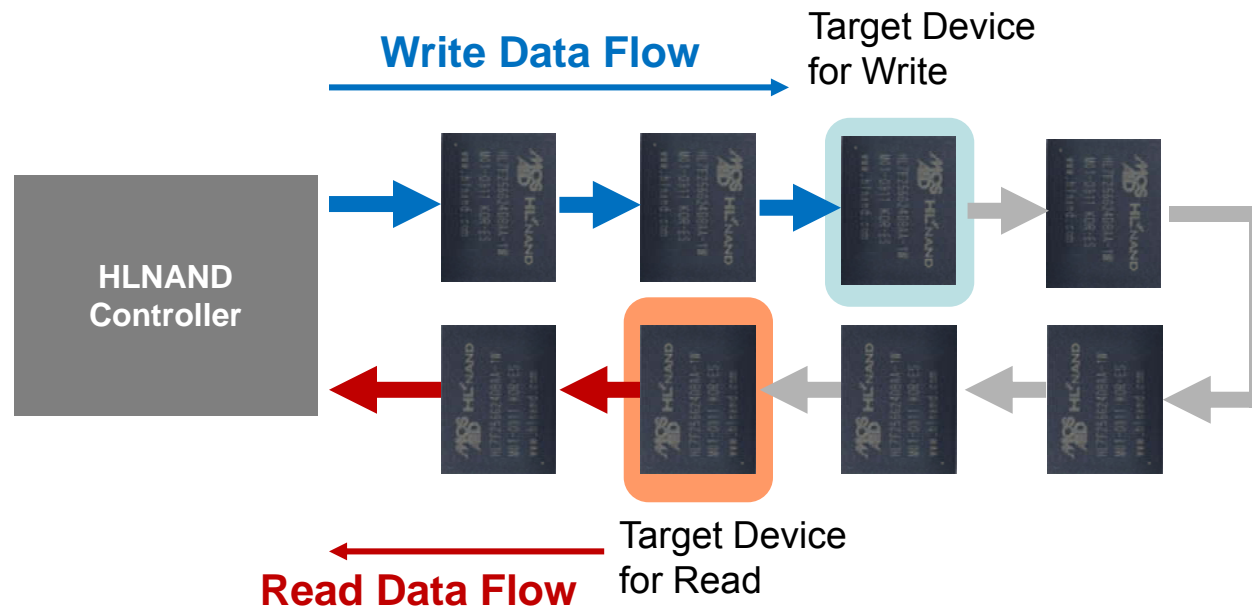
DDR-834 @417MHz

HLNAND/HLNAND2 Key Features

- DuplexRW™ (QDR533/QDR 1600):
Simultaneous Read/Write operations,
effective 533MBs/1600MBs data
throughput
- Built-in EDC (Error Detection Code), on
and off control
- Packet truncation for saving power
- Independent automatic status bus -
separate status ring (STI/STO)

DuplexRW™ (QDR Operation)

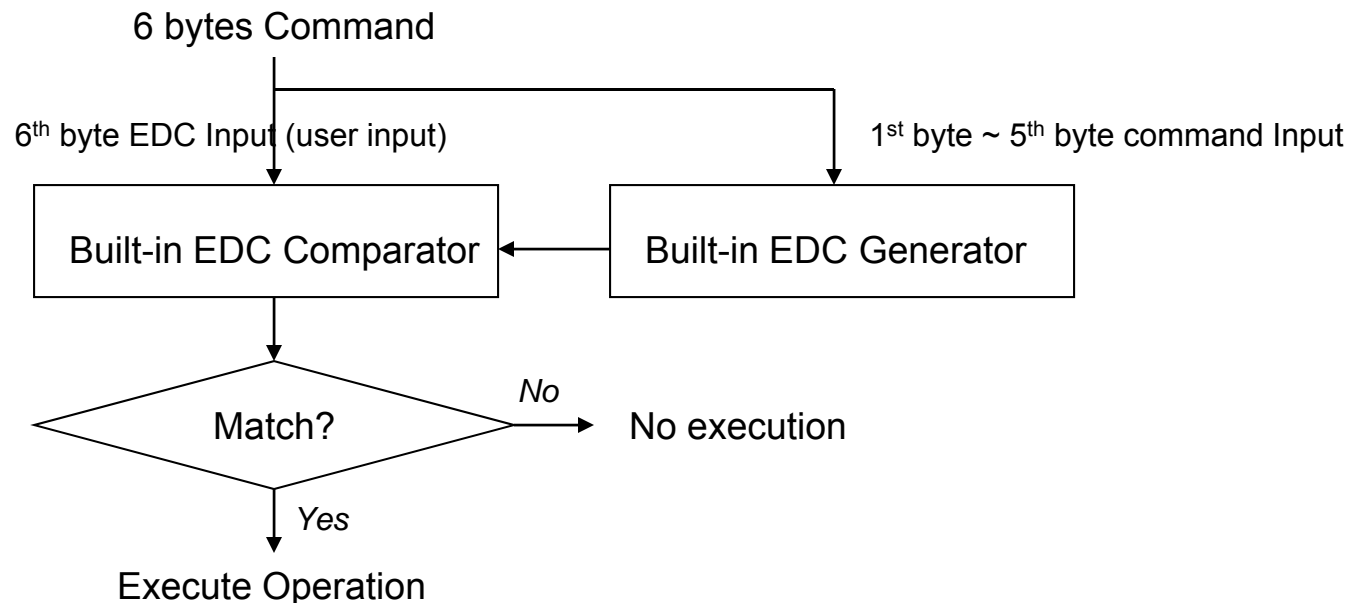
- Simultaneously write to upstream device while reading from downstream device
- Effectively doubles data throughput
 - HLNAND: doubled to 533MB/s
 - HLNAND2: doubled to 1600MB/s



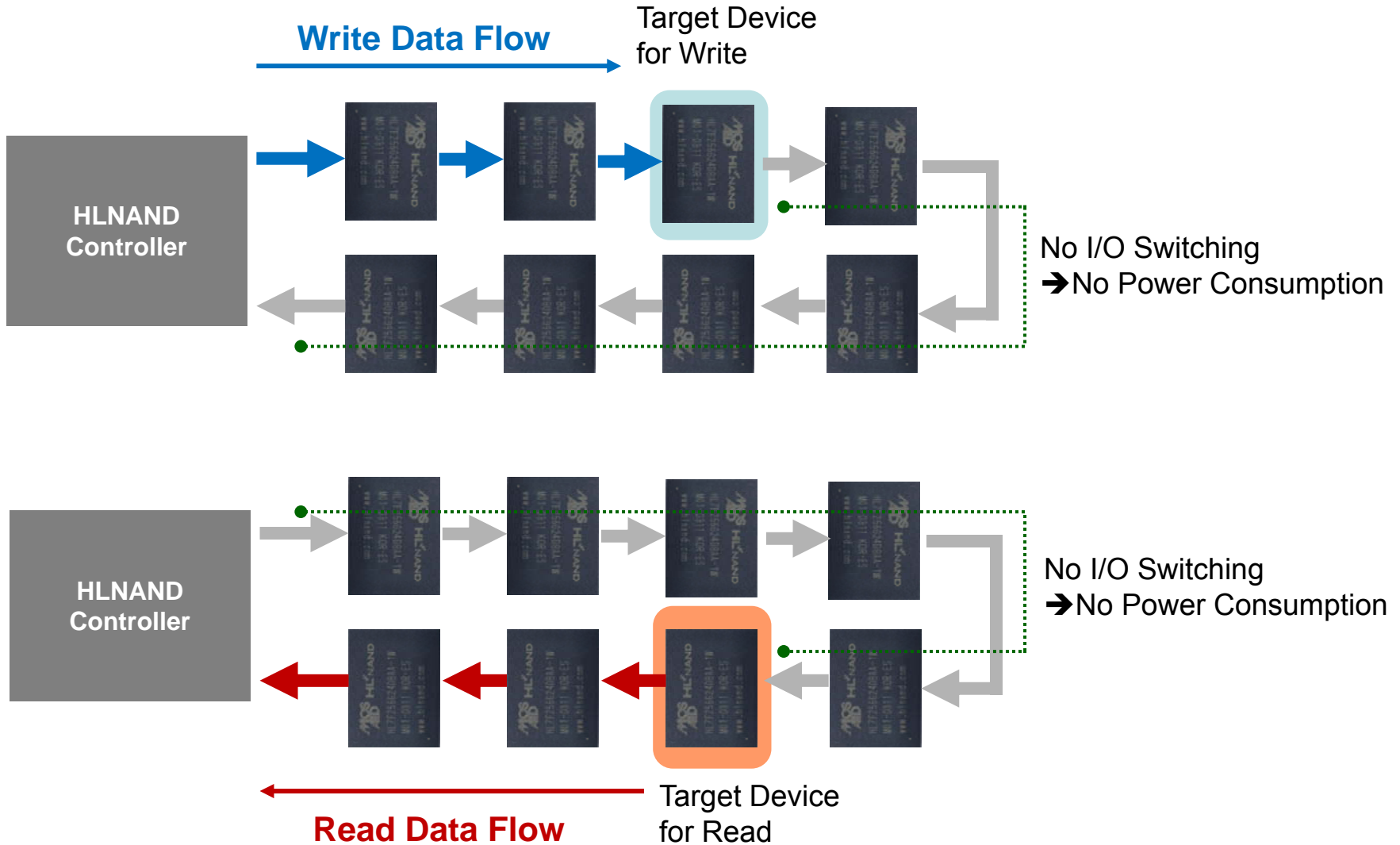
Built-in EDC (Error Detection Code)

6-byte Command Architecture

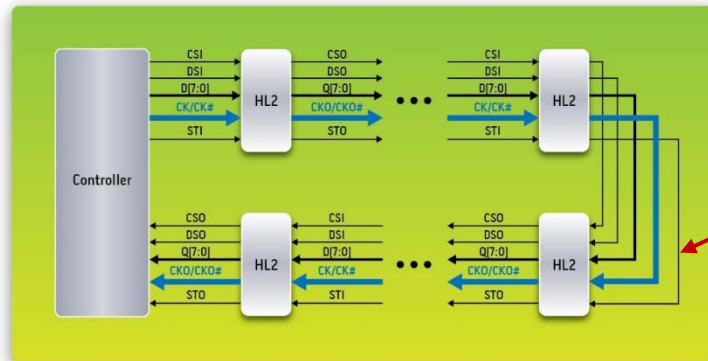
1 st Byte	2 nd Byte	3 rd Byte	4 th Byte	5 th Byte	6 th Byte
Device ID	OP Code	ADD1	ADD2	ADD3	EDC



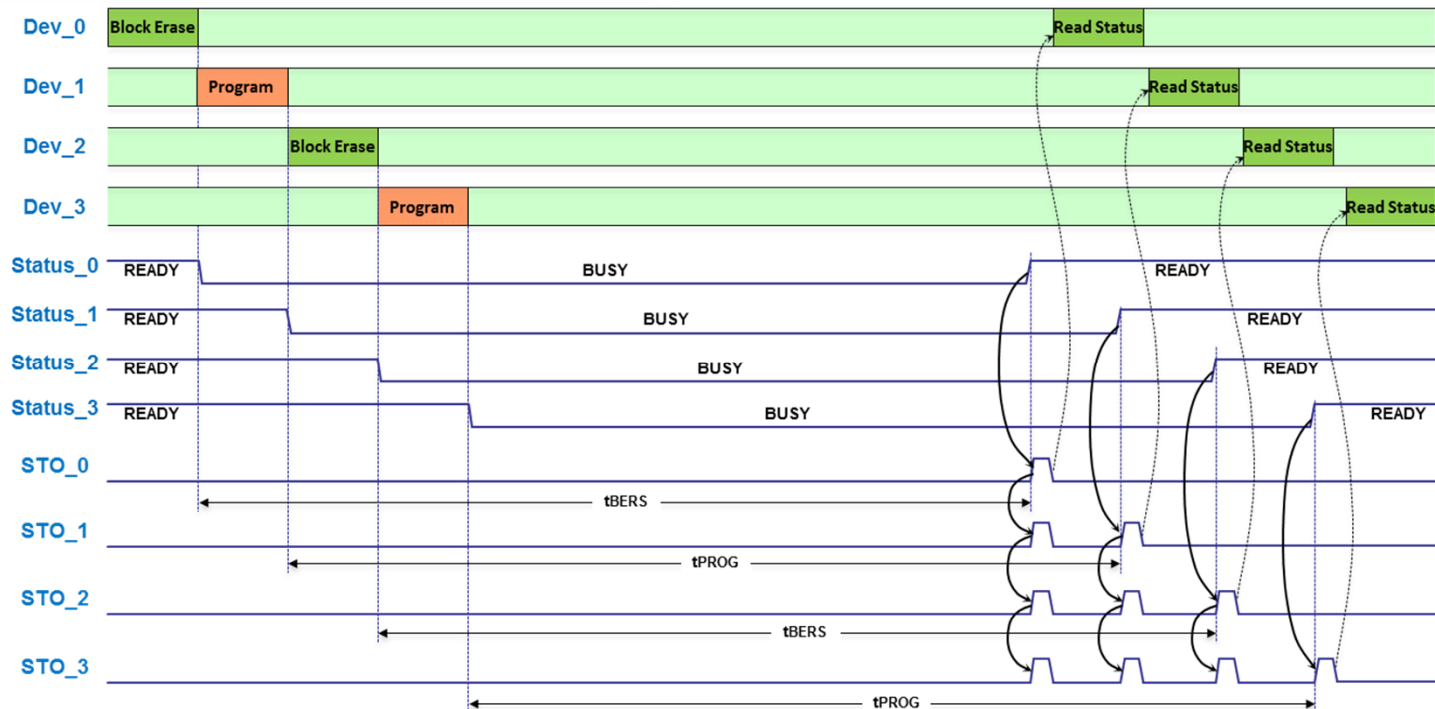
Packet Truncation



Independent Automatic Status Bus



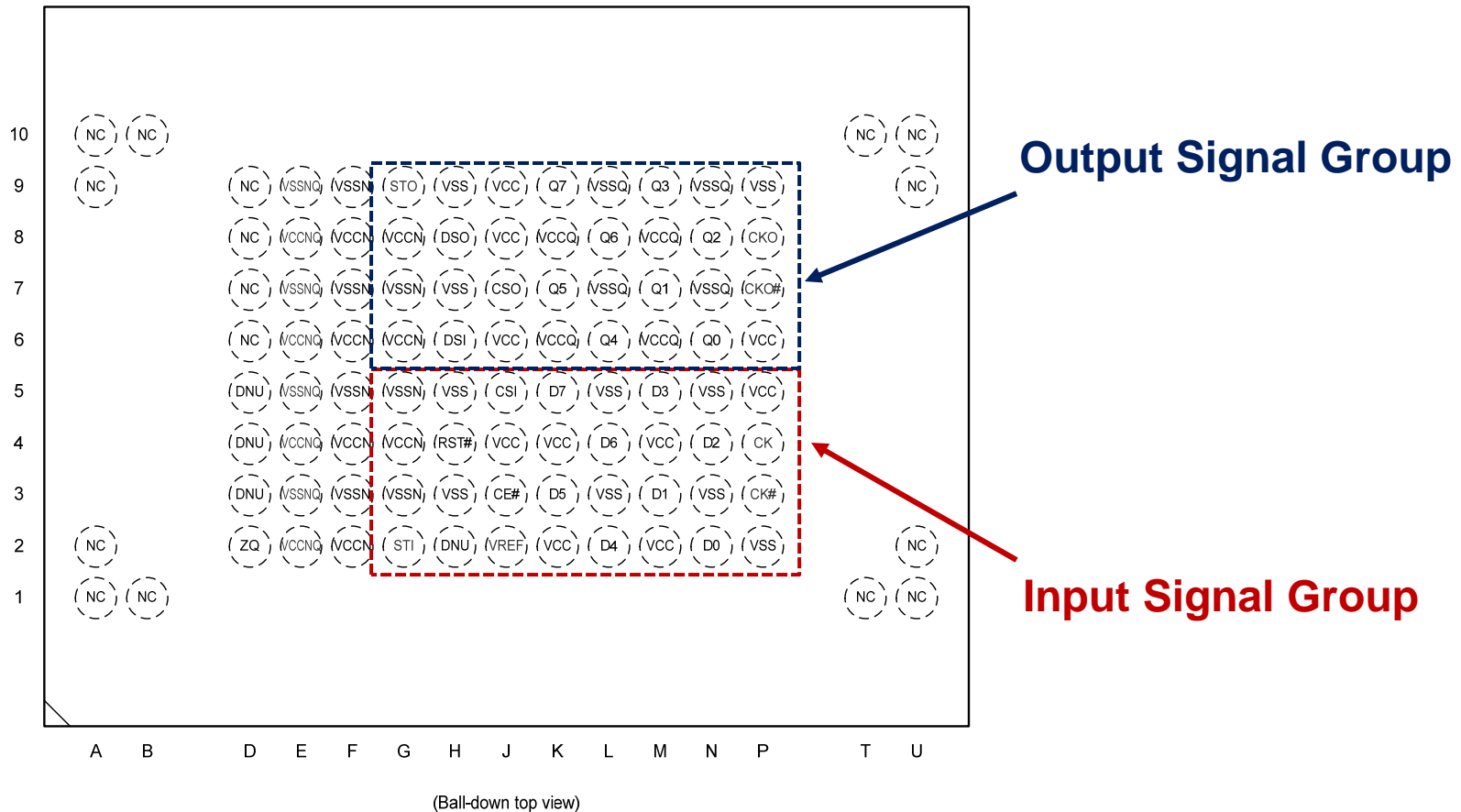
Separate Status Ring (STI/STO)



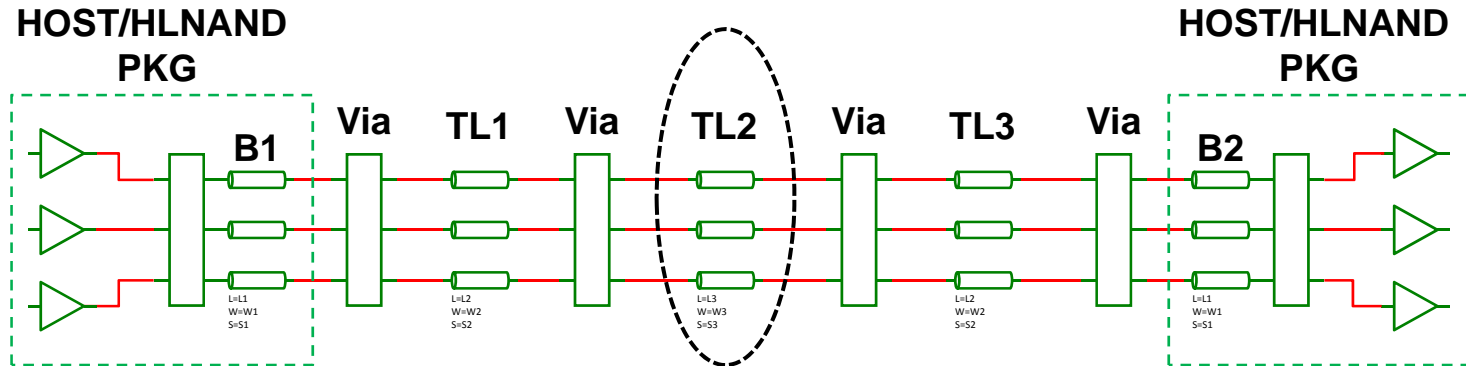
Agenda

- Introduction
- HyperLink NAND (HLNAND)
Flash Technology
- **Signal Integrity**
- Summary

HLNAND2 Signal Integrity (Signal to Ball Assignment)



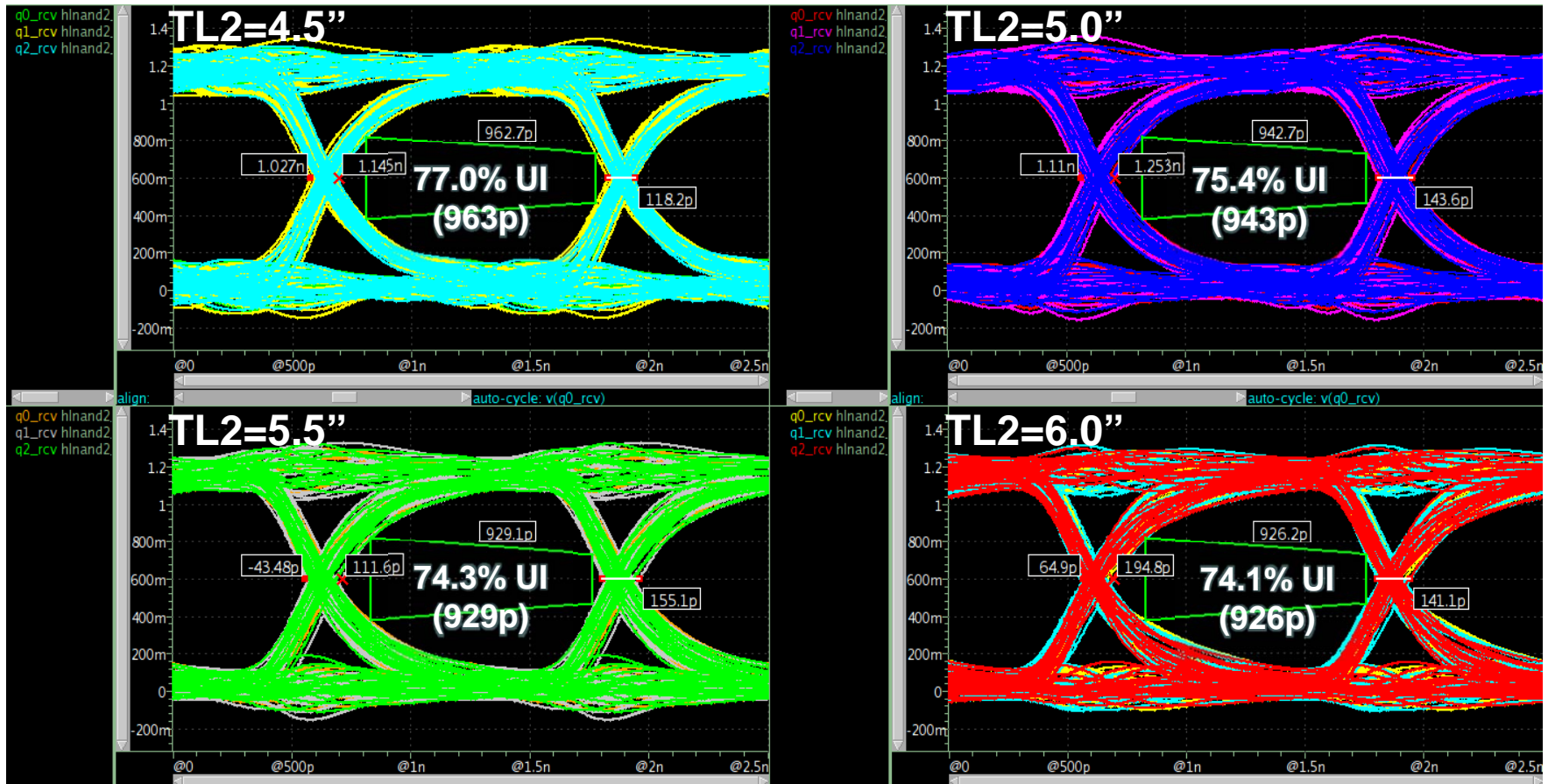
HLNAND2 Signal Integrity (General Topology Model)



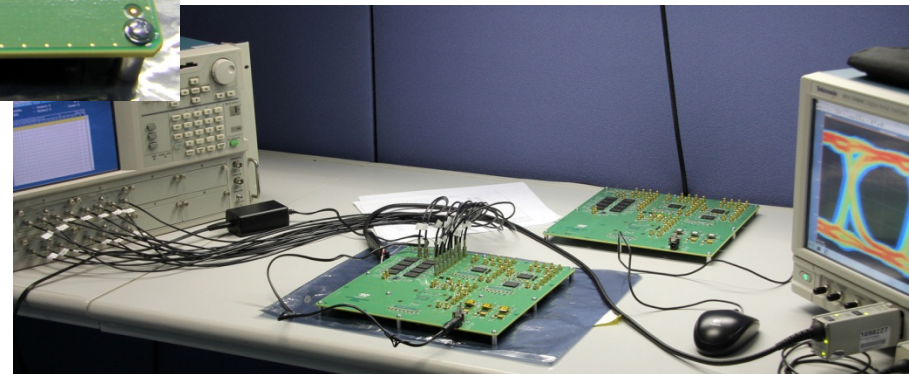
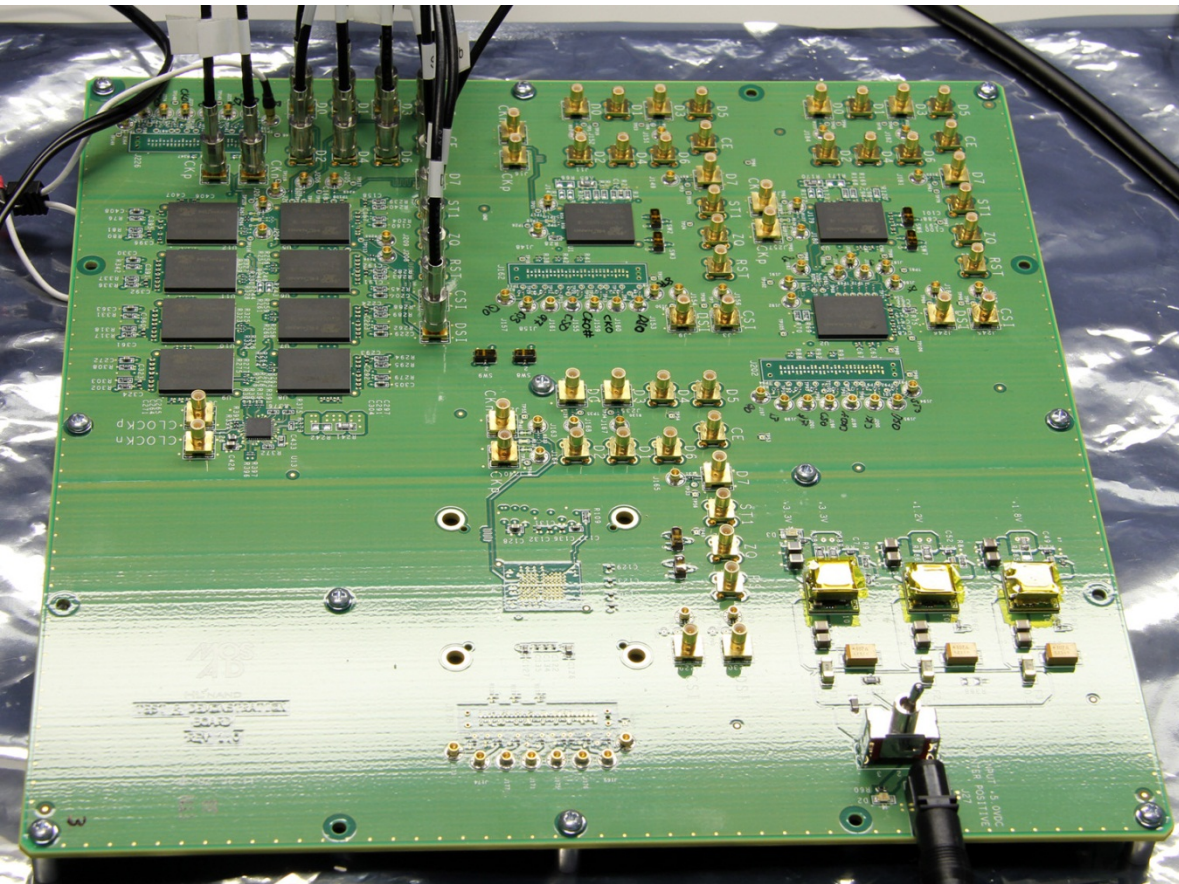
- 3 Line Model for X-talk
- PCB Impedance = $50 \Omega \pm 7.5 \Omega$
- Space of Lines = 4 and 8 mil
- Min. time width of RCV eye window = $0.66U_I$
- Driver Strength = 50Ω
- ODT is not required

HLNAND2 SI Simulation

(DDR-800 Point-To-Point, No Termination)

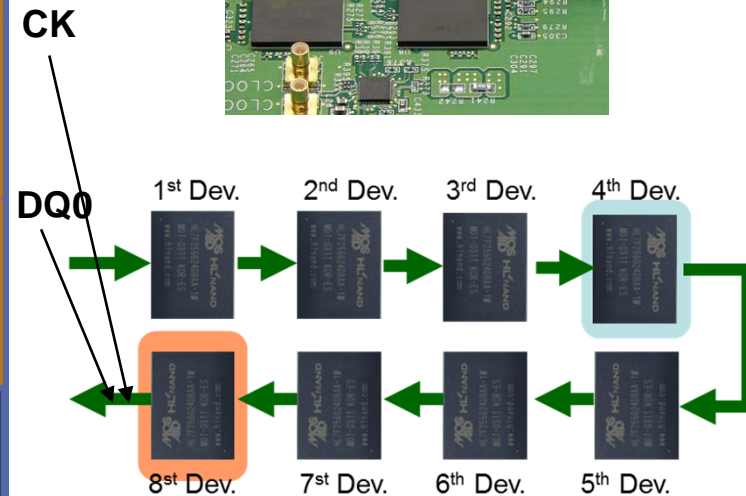
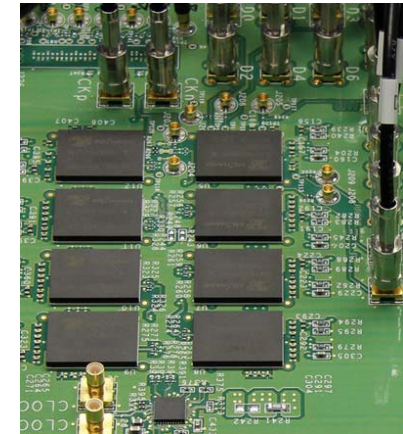


HLNAND2 Test Board



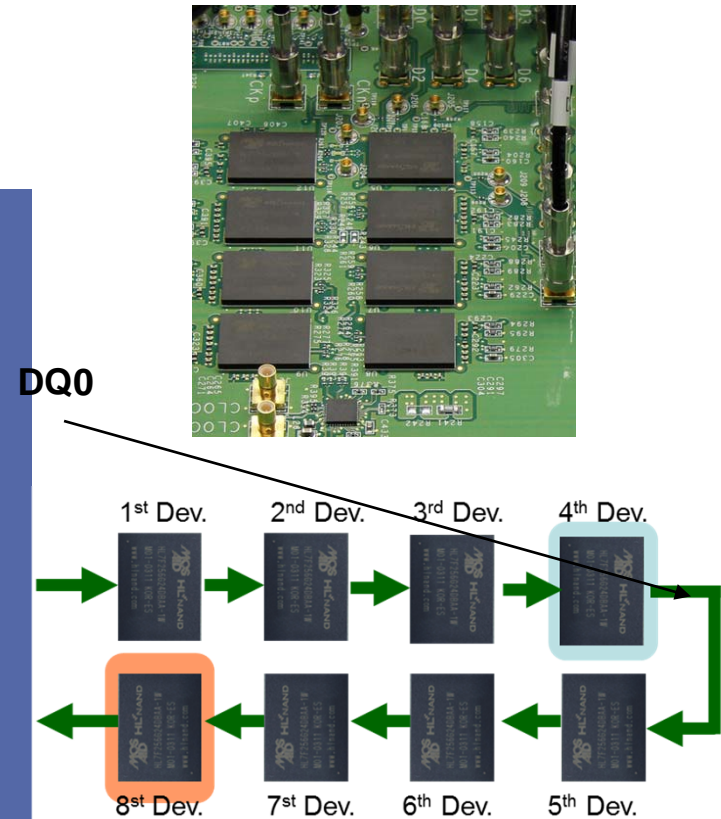
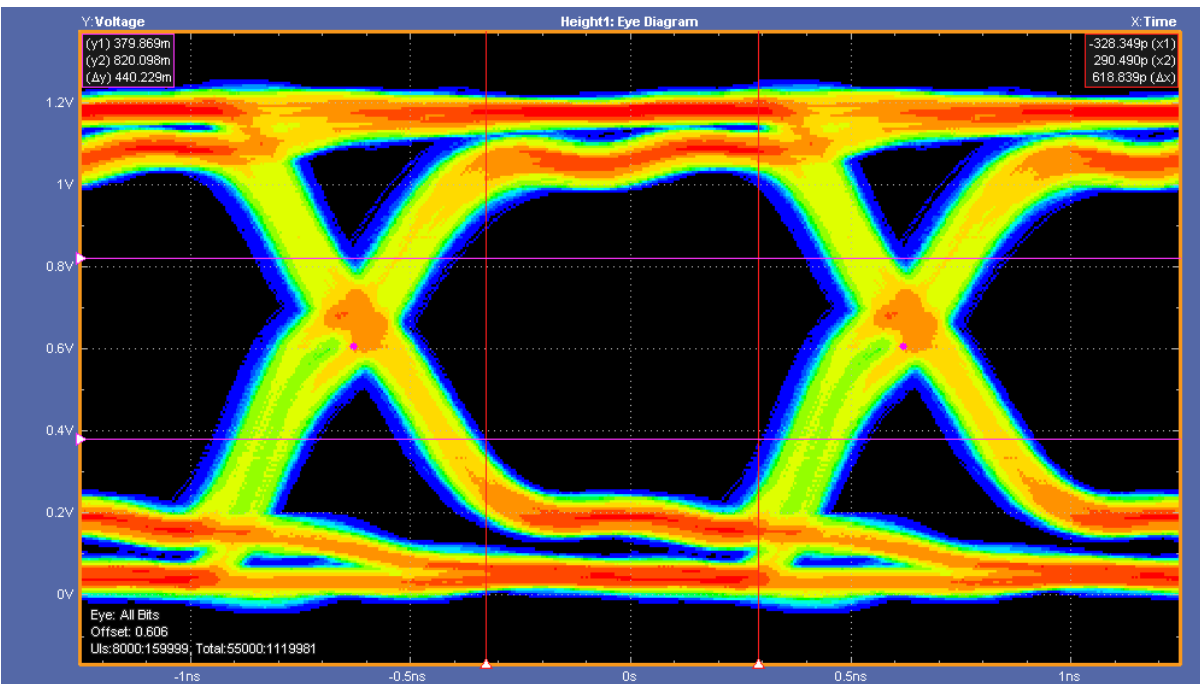
Measured Signal

(CK Output/DQ Signals from 8th Dev. @DDR800)



Measured Data Eye

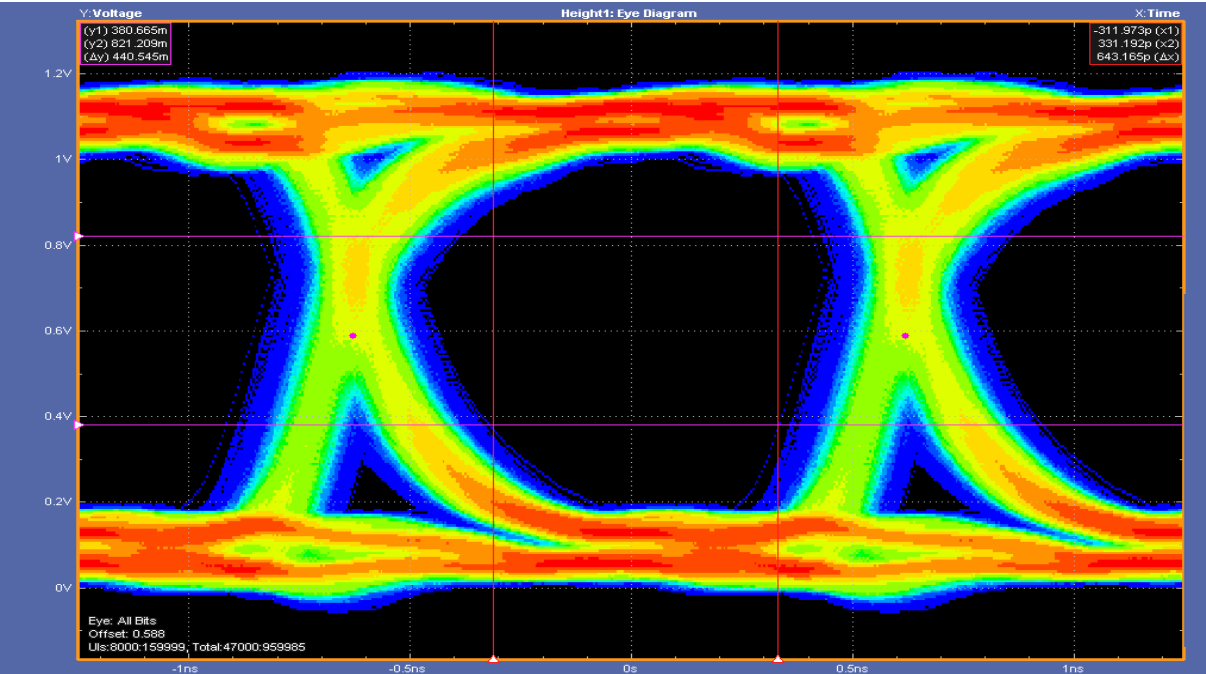
(DQ Signals from 4th Dev. @DDR800)



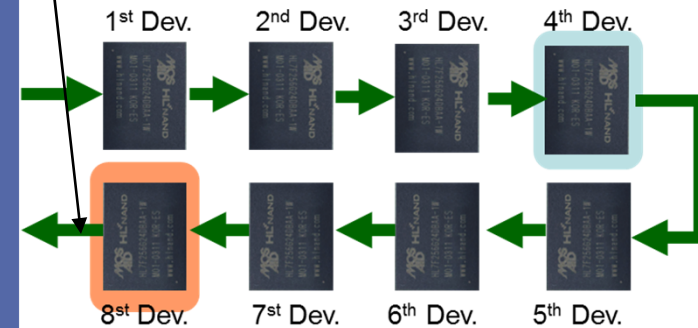
Measured Data Eye

(DQ Signals from 8th Dev. @DDR800)

DQ0 (Data Eye)



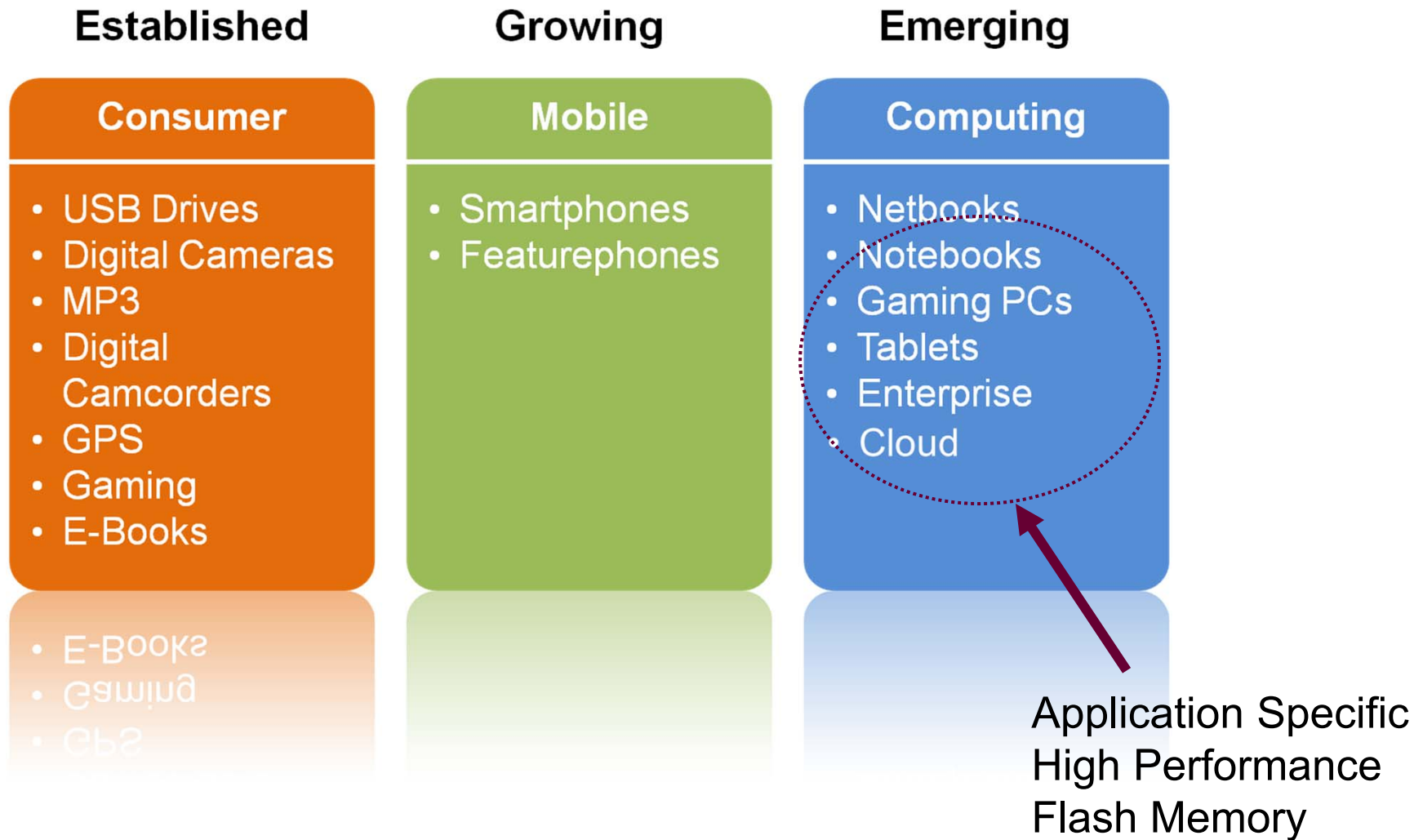
DQ0



Agenda

- Introduction
- HyperLink NAND (HLNAND)
Flash Technology
- Signal Integrity
- **Summary**

HLNAND Target Market



HLNAND Applications

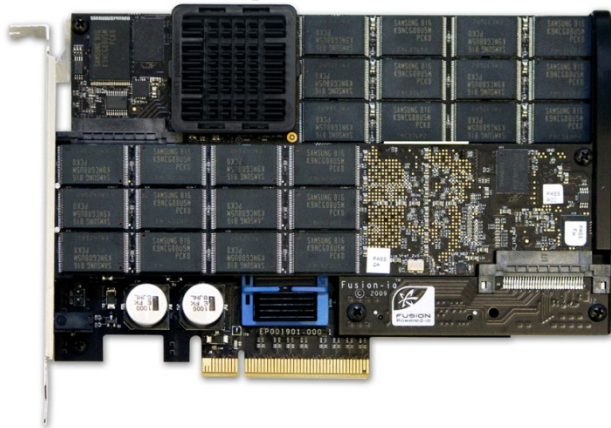
Consumer SSD



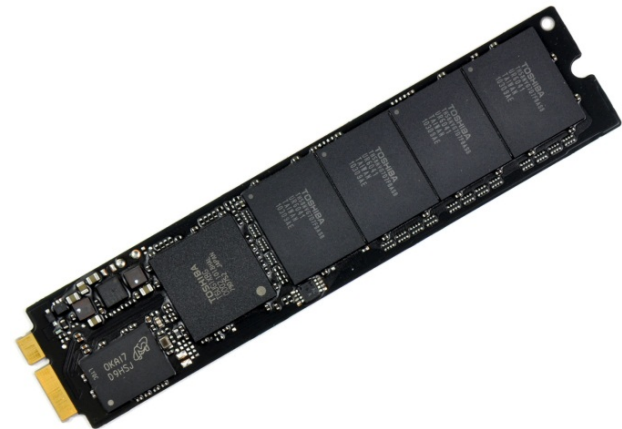
Embedded Flash



Enterprise SSD

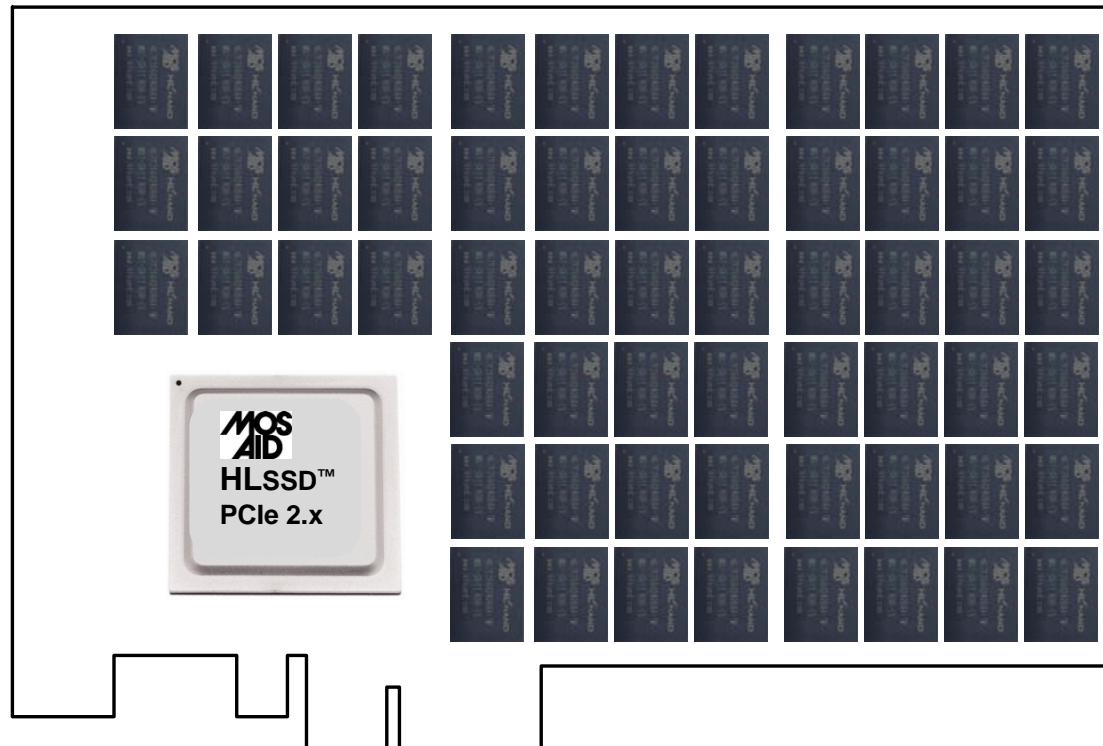


SSD Modules



HLSSD Development

- Native PCIe Flash Controller (ASIC/FPGA)
- X4 or x8 PCIe Gen2/Gen3
- TB Capacity
- GB/s-Performance



HLNAND Flash Benefits

Higher Performance

Longer System Longevity*

Lower Power Consumption

High Scalability

Interface Extensibility


Advanced Features

Reduced Overall Cost


* Monolithic HLNAND

Resource for HLNAND Flash

www.HLNAND.com



A NEW STANDARD FOR
HIGH-PERFORMANCE
FLASH MEMORY



HOME TECHNOLOGY PUBLICATIONS NEWS & EVENTS PARTNERS CONTACT US

WHAT'S NEW

Nov 2/11 **MOSAID Unveils Industry's Fastest Flash Memory Device**

Jul 19/11 **MOSAID Demonstrates Production-Ready 256Gb HLNAND Flash Memory Device**

Feb 24/11 **MOSAID Introduces HLNAND2 Flash Memory Specification**

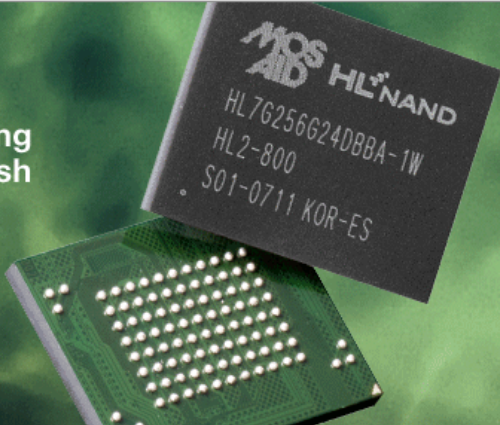
Jul 28/10 **MOSAID Showcases Solid State Drive Prototype**

INNOVATIONS

MOSAID now sampling industry's fastest Flash Memory device

256Gb HLNAND2 operating at DDR800

[LEARN MORE](#)




PARTNER LOGIN

Username:

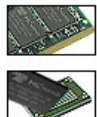
Password: [SEND](#)

[Register](#) | [Forgot Password](#)


PUBLICATIONS



White Paper
Enabling Ultra-High Bandwidth Scalable SSDs with HLNAND



64GB HLNAND Flash Module Brief
64Gb HLNAND Flash MCP Brief



256GB HLNAND2Flash MCP Brief

HLNAND™ is a technology developed by MOSAID that is available for licensing from MOSAID
Copyright © 2011 MOSAID Technologies Incorporated. All rights reserved. [Terms](#) | [Privacy Policy](#) & [Code](#)